



**THE DATASHEET OF
TPIC6B273DW**



- Low $r_{DS(on)}$. . . 5 Ω Typical
- Avalanche Energy . . . 30 mJ
- Eight Power DMOS-Transistor Outputs of 150-mA Continuous Current
- 500-mA Typical Current-Limiting Capability
- Output Clamp Voltage . . . 50 V
- Low Power Consumption

description

The TPIC6B273 is a monolithic, high-voltage, medium-current, power logic octal D-type latch with DMOS-transistor outputs designed for use in systems that require relatively high load power. The device contains a built-in voltage clamp on the outputs for inductive transient protection. Power driver applications include relays, solenoids, and other medium-current or high-voltage loads.

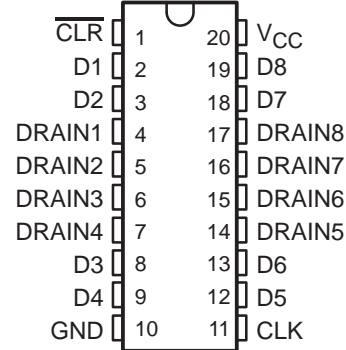
The TPIC6B273 contains eight positive-edge-triggered D-type flip-flops with a direct clear input. Each flip-flop features an open-drain power DMOS-transistor output.

When clear (\overline{CLR}) is high, information at the D inputs meeting the setup time requirements is transferred to the DRAIN outputs on the positive-going edge of the clock (CLK) pulse. Clock triggering occurs at a particular voltage level and is not directly related to the transition time of the positive-going pulse. When the clock input (CLK) is at either the high or low level, the D input signal has no effect at the output. An asynchronous \overline{CLR} is provided to turn all eight DMOS-transistor outputs off. When data is low for a given output, the DMOS-transistor output is off. When data is high, the DMOS-transistor output has sink-current capability.

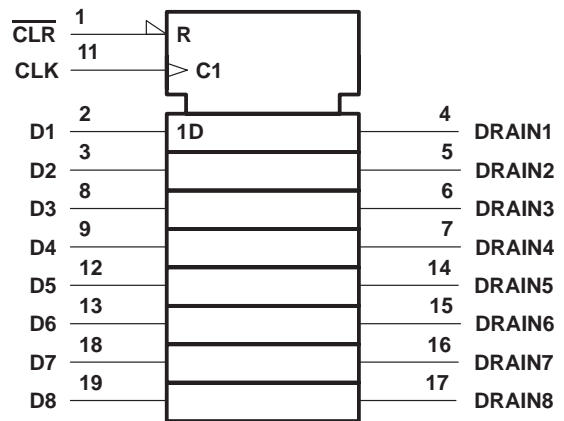
Outputs are low-side, open-drain DMOS transistors with output ratings of 50 V and 150-mA continuous sink-current capability. Each output provides a 500-mA typical current limit at $T_C = 25^\circ\text{C}$. The current limit decreases as the junction temperature increases for additional device protection.

The TPIC6B273 is characterized for operation over the operating case temperature range of -40°C to 125°C .

DW OR N PACKAGE
(TOP VIEW)



logic symbol†



† This symbol is in accordance with ANSI/IEEE Standard 91-1984 and IEC Publication 617-12.

FUNCTION TABLE
(each channel)

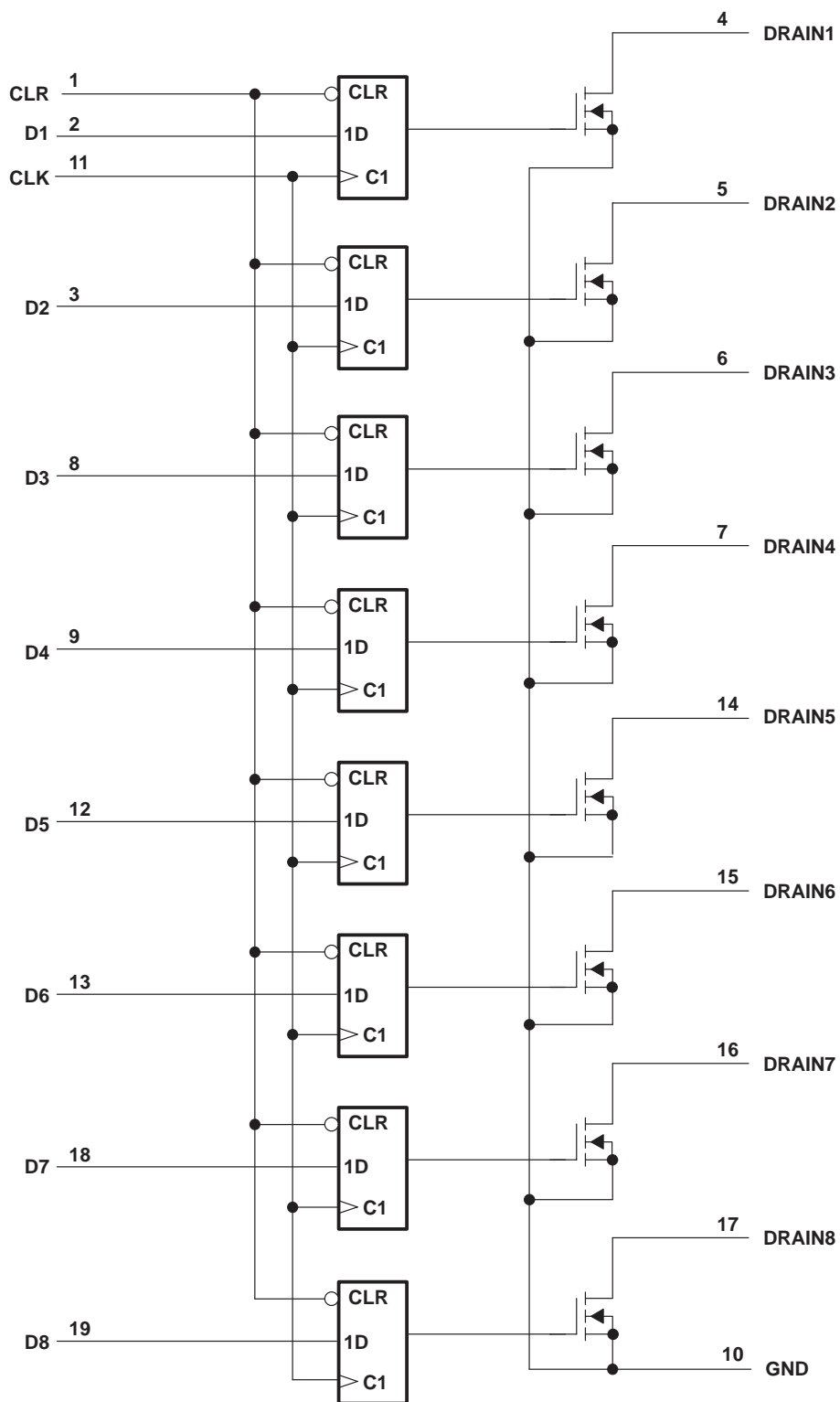
| \overline{CLR} | INPUTS | | OUTPUT DRAIN |
|------------------|------------|---|-----------------|
| | CLK | D | |
| L | X | X | H |
| H | \uparrow | H | L |
| H | \uparrow | L | H |
| H | L | X | Latched |

H = high level, L = low level, X = irrelevant

TPIC6B273 POWER LOGIC OCTAL D-TYPE LATCH

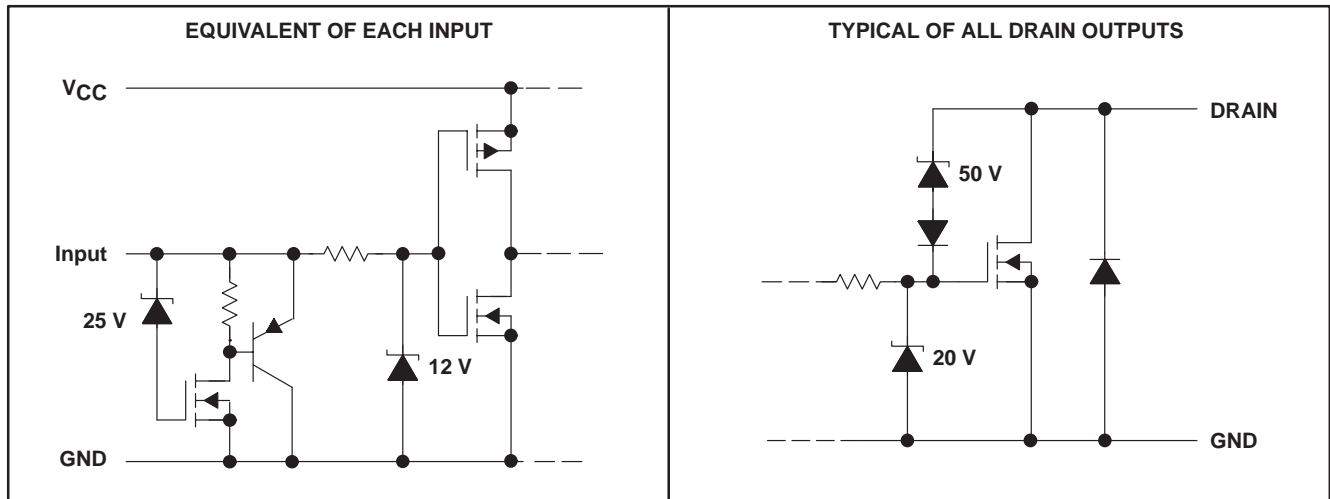
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logic diagram (positive logic)



POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

schematic of inputs and outputs



absolute maximum ratings over recommended operating case temperature range (unless otherwise noted)†

| | |
|--|------------------------------|
| Logic supply voltage, V_{CC} (see Note 1) | 7 V |
| Logic input voltage range, V_I | -0.3 V to 7 V |
| Power DMOS drain-to-source voltage, V_{DS} (see Note 2) | 50 V |
| Continuous source-to-drain diode anode current | 500 mA |
| Pulsed source-to-drain diode anode current (see Note 3) | 1 A |
| Pulsed drain current, each output, all outputs on, I_D , $T_C = 25^\circ\text{C}$ (see Note 3) | 500 mA |
| Continuous drain current, each output, all outputs on, I_D , $T_C = 25^\circ\text{C}$ | 150 mA |
| Peak drain current single output, I_{DM} , $T_C = 25^\circ\text{C}$ (see Note 3) | 500 mA |
| Single-pulse avalanche energy, E_{AS} (see Figure 4) | 30 mJ |
| Avalanche current, I_{AS} (see Note 4) | 500 mA |
| Continuous total dissipation | See Dissipation Rating Table |
| Operating virtual junction temperature range, T_J | -40°C to 150°C |
| Operating case temperature range, T_C | -40°C to 125°C |
| Storage temperature range | -65°C to 150°C |
| Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds | 260°C |

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES:
1. All voltage values are with respect to GND.
 2. Each power DMOS source is internally connected to GND.
 3. Pulse duration $\leq 100 \mu\text{s}$ and duty cycle $\leq 2\%$.
 4. DRAIN supply voltage = 15 V, starting junction temperature (T_{JS}) = 25°C, $L = 200 \text{ mH}$, $I_{AS} = 0.5 \text{ A}$ (see Figure 4).

DISSIPATION RATING TABLE

| PACKAGE | $T_C \leq 25^\circ\text{C}$ POWER RATING | DERATING FACTOR ABOVE $T_C = 25^\circ\text{C}$ | $T_C = 125^\circ\text{C}$ POWER RATING |
|---------|---|---|---|
| DW | 1389 mW | 11.1 mW/°C | 278 mW |
| N | 1050 mW | 10.5 mW/°C | 263 mW |

TPIC6B273

POWER LOGIC OCTAL D-TYPE LATCH

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recommended operating conditions

| | MIN | MAX | UNIT |
|---|---------------|-----|------------------|
| Logic supply voltage, V_{CC} | 4.5 | 5.5 | V |
| High-level input voltage, V_{IH} | 0.85 V_{CC} | | V |
| Low-level input voltage, V_{IL} | 0.15 V_{CC} | | V |
| Pulsed drain output current, $T_C = 25^\circ\text{C}$, $V_{CC} = 5\text{ V}$ (see Notes 3 and 5) | -500 | 500 | mA |
| Setup time, D high before $\text{CLK}\uparrow$, t_{SU} (see Figure 2) | 20 | | ns |
| Hold time, D high after $\text{CLK}\uparrow$, t_H (see Figure 2) | 20 | | ns |
| Pulse duration, t_W (see Figure 2) | 40 | | ns |
| Operating case temperature, T_C | -40 | 125 | $^\circ\text{C}$ |

electrical characteristics, $V_{CC} = 5\text{ V}$, $T_C = 25^\circ\text{C}$ (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|---|---|--|------|-----|---------------|
| $V_{(BR)DSX}$ Drain-to-source breakdown voltage | $I_D = 1\text{ mA}$ | 50 | | | V |
| V_{SD} Source-to-drain diode forward voltage | $I_F = 100\text{ mA}$ | | 0.85 | 1 | V |
| I_{IH} High-level input current | $V_{CC} = 5.5\text{ V}$, $V_I = V_{CC}$ | | | 1 | μA |
| I_{IL} Low-level input current | $V_{CC} = 5.5\text{ V}$, $V_I = 0$ | | | -1 | μA |
| I_{CC} Logic supply current | $V_{CC} = 5.5\text{ V}$ | All outputs off | 20 | 100 | μA |
| | | All outputs on | 150 | 300 | |
| I_N Nominal current | $V_{DS(on)} = 0.5\text{ V}$, $I_N = I_D$, $T_C = 85^\circ\text{C}$, See Notes 5, 6, and 7 | | 90 | | mA |
| I_{DSX} Off-state drain current | $V_{DS} = 40\text{ V}$, $V_{CC} = 5.5\text{ V}$ | | 0.1 | 5 | μA |
| | $V_{DS} = 40\text{ V}$, $V_{CC} = 5.5\text{ V}$, $T_C = 125^\circ\text{C}$ | | 0.15 | 8 | |
| $r_{DS(on)}$ Static drain-to-source on-state resistance | $I_D = 100\text{ mA}$, $V_{CC} = 4.5\text{ V}$ | See Notes 5 and 6 and Figures 6 and 7 | 4.2 | 5.7 | Ω |
| | $I_D = 100\text{ mA}$, $V_{CC} = 4.5\text{ V}$, $T_C = 125^\circ\text{C}$ | | 6.8 | 9.5 | |
| | $I_D = 350\text{ mA}$, $V_{CC} = 4.5\text{ V}$ | | 5.5 | 8 | |

switching characteristics, $V_{CC} = 5\text{ V}$, $T_C = 25^\circ\text{C}$

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|---|---|-----|-----|-----|------|
| t_{PLH} Propagation delay time, low-to-high-level output from CLK | $C_L = 30\text{ pF}$, $I_D = 100\text{ mA}$, See Figures 1, 2, and 8 | | 150 | | ns |
| t_{PHL} Propagation delay time, high-to-low-level output from CLK | | | 90 | | ns |
| t_r Rise time, drain output | | | 200 | | ns |
| t_f Fall time, drain output | | | 200 | | ns |
| t_a Reverse-recovery-current rise time | $I_F = 100\text{ mA}$, $di/dt = 20\text{ A}/\mu\text{s}$, See Notes 5 and 6 and Figure 3 | | 100 | | ns |
| t_{rr} Reverse-recovery time | | | 300 | | |

- NOTES: 3. Pulse duration $\leq 100\ \mu\text{s}$ and duty cycle $\leq 2\%$.
 5. Technique should limit $T_J - T_C$ to 10°C maximum.
 6. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts.
 7. Nominal current is defined for a voltage comparison between devices from different sources. It is the current that produces a voltage drop of 0.5 V at $T_C = 85^\circ\text{C}$.



thermal resistance

| PARAMETER | | TEST CONDITIONS | MIN | MAX | UNIT |
|------------------|---|-----------------|--------------------------------|-----|------|
| R _{θJA} | Thermal resistance, junction-to-ambient | DW package | | 90 | °C/W |
| | | N package | All 8 outputs with equal power | 95 | |

PARAMETER MEASUREMENT INFORMATION

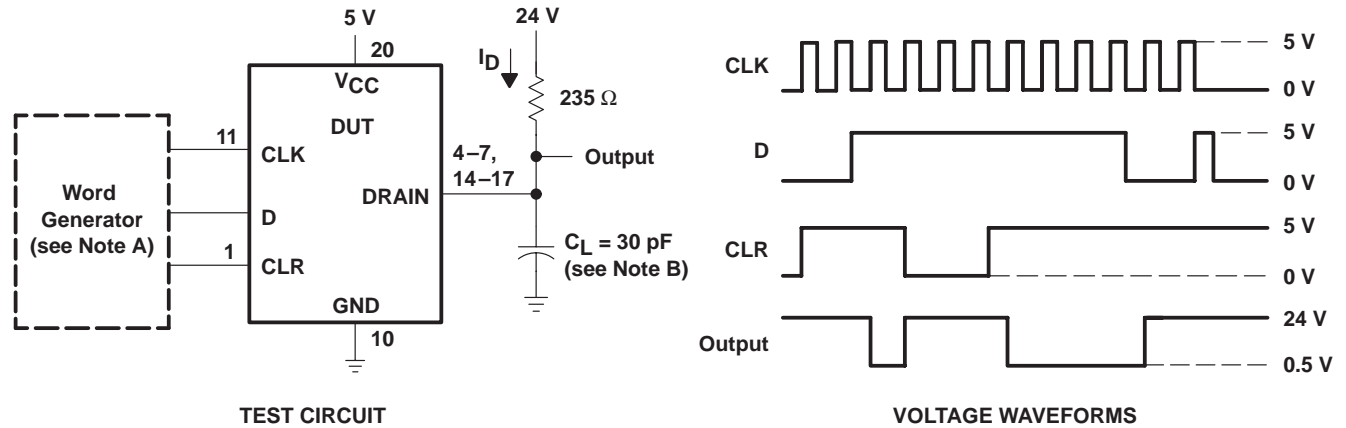


Figure 1. Resistive-Load Test Circuit and Voltage Waveforms

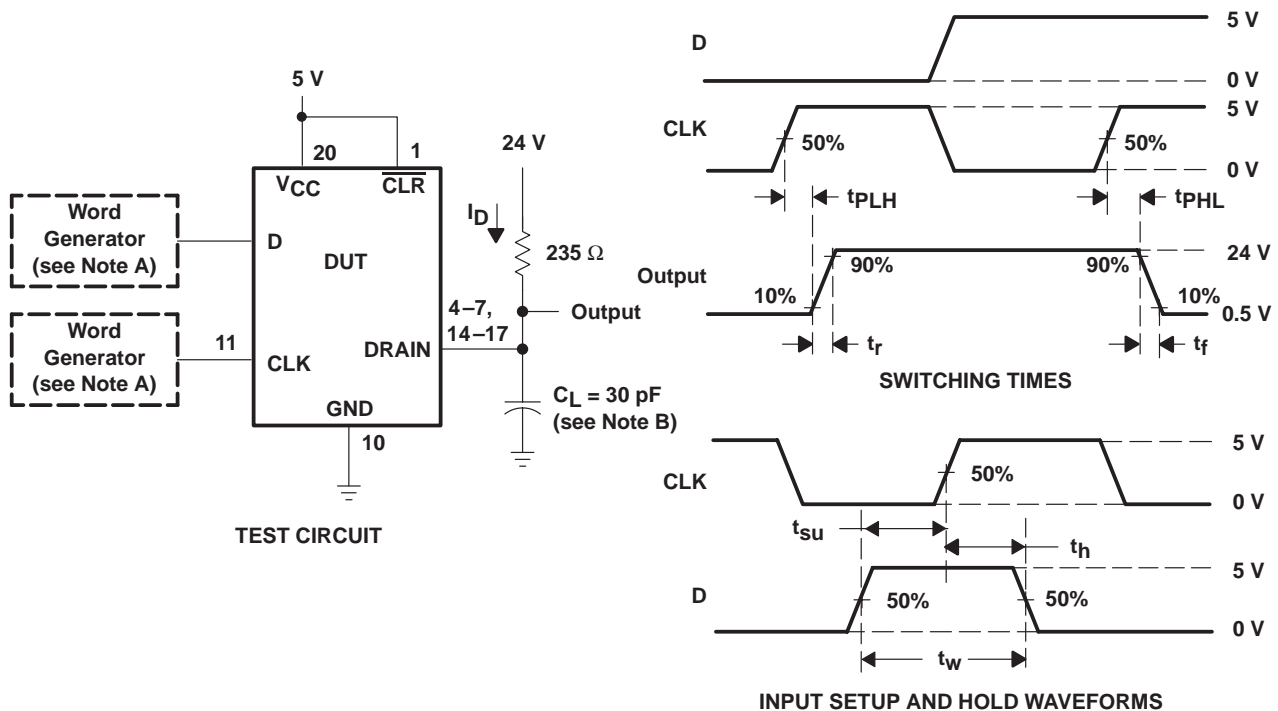


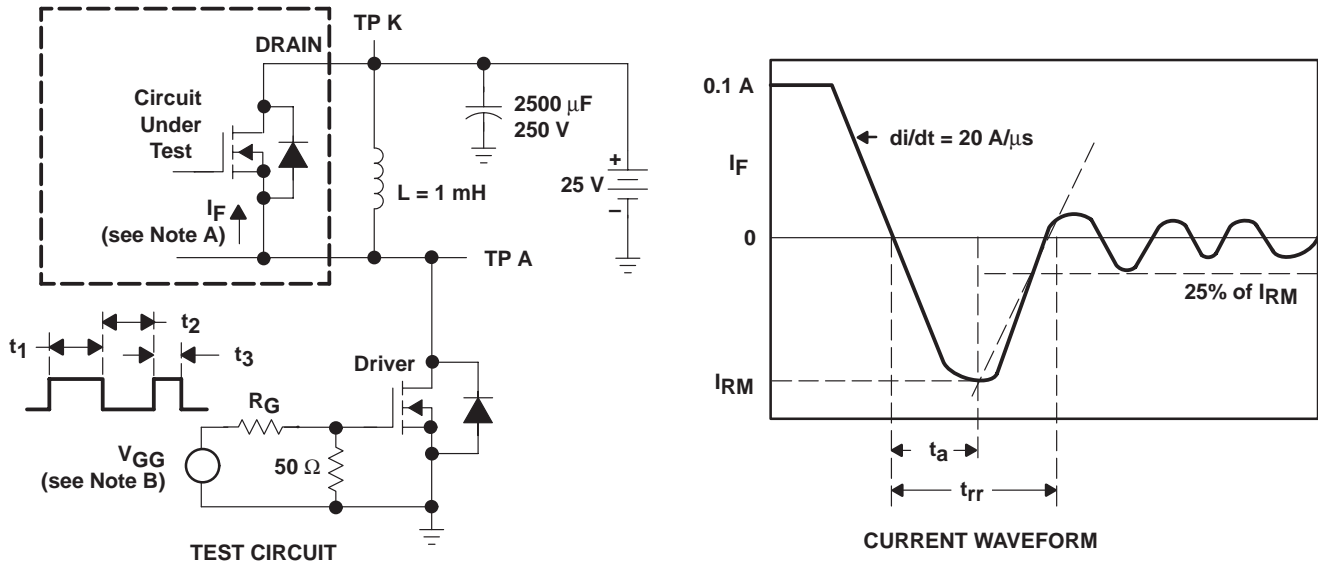
Figure 2. Test Circuit, Switching Times, and Voltage Waveforms

- NOTES: A. The word generator has the following characteristics: $t_r \leq 10$ ns, $t_f \leq 10$ ns, $t_w = 300$ ns, pulsed repetition rate (PRR) = 5 KHz, $Z_O = 50 \Omega$.
B. C_L includes probe and jig capacitance.

TPIC6B273 POWER LOGIC OCTAL D-TYPE LATCH

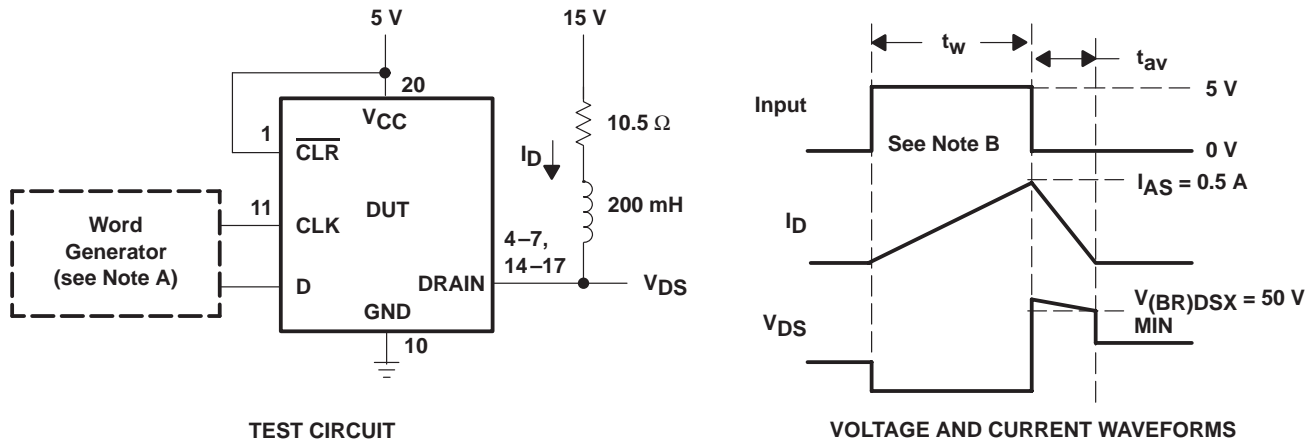
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PARAMETER MEASUREMENT INFORMATION



- NOTES: A. The DRAIN terminal under test is connected to the TP K test point. All other terminals are connected together and connected to the TP A test point.
 B. The V_{GG} amplitude and R_G are adjusted for $di/dt = 20 \text{ A}/\mu\text{s}$. A V_{GG} double-pulse train is used to set $I_F = 0.1 \text{ A}$, where $t_1 = 10 \mu\text{s}$, $t_2 = 7 \mu\text{s}$, and $t_3 = 3 \mu\text{s}$.

Figure 3. Reverse-Recovery-Current Test Circuit and Waveforms of Source-to-Drain Diode



- NOTES: A. The word generator has the following characteristics: $t_r \leq 10 \text{ ns}$, $t_f \leq 10 \text{ ns}$, $Z_O = 50 \Omega$.
 B. Input pulse duration, t_w , is increased until peak current $I_{AS} = 0.5 \text{ A}$.
 Energy test is defined as $E_{AS} = I_{AS} \times V_{(BR)DSX} \times t_{av}/2 = 30 \text{ mJ}$.

Figure 4. Single-Pulse Avalanche Energy Test Circuit and Waveforms

TYPICAL CHARACTERISTICS

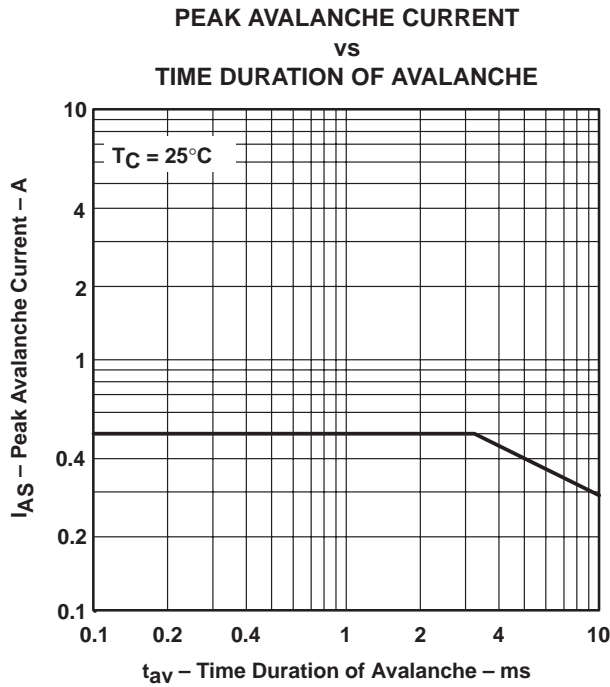


Figure 5

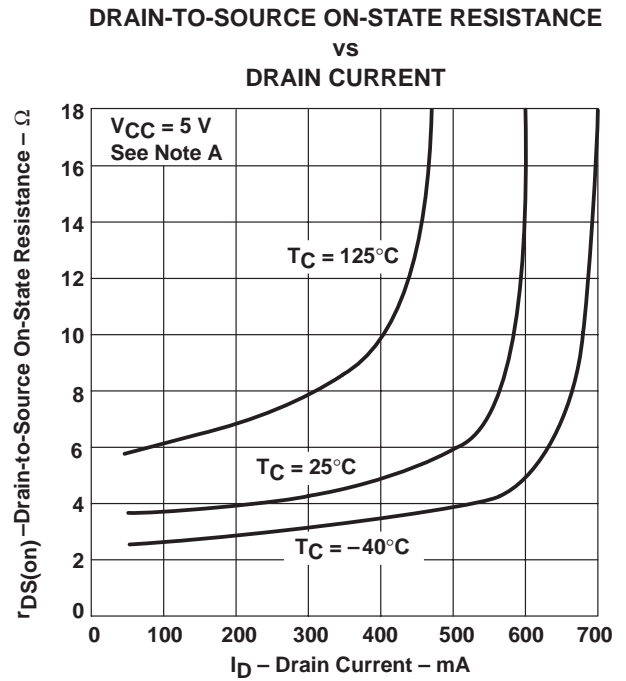


Figure 6

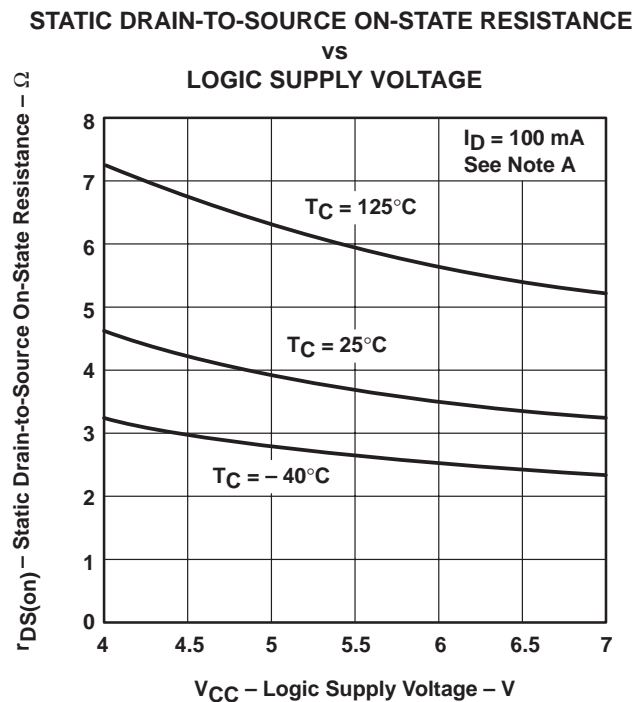


Figure 7

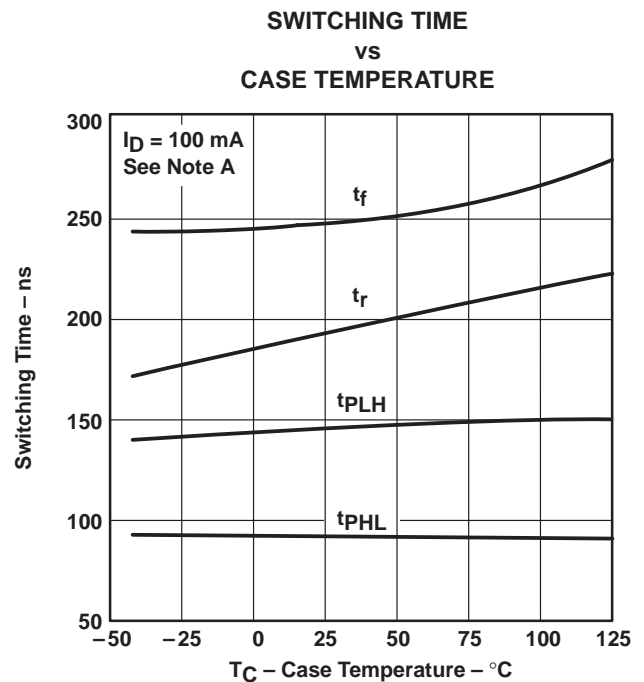


Figure 8

NOTE C: Technique should limit $T_J - T_C$ to 10°C maximum.

TPIC6B273 POWER LOGIC OCTAL D-TYPE LATCH

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THERMAL INFORMATION

**MAXIMUM CONTINUOUS
DRAIN CURRENT OF EACH OUTPUT
vs
NUMBER OF OUTPUTS CONDUCTING
SIMULTANEOUSLY**

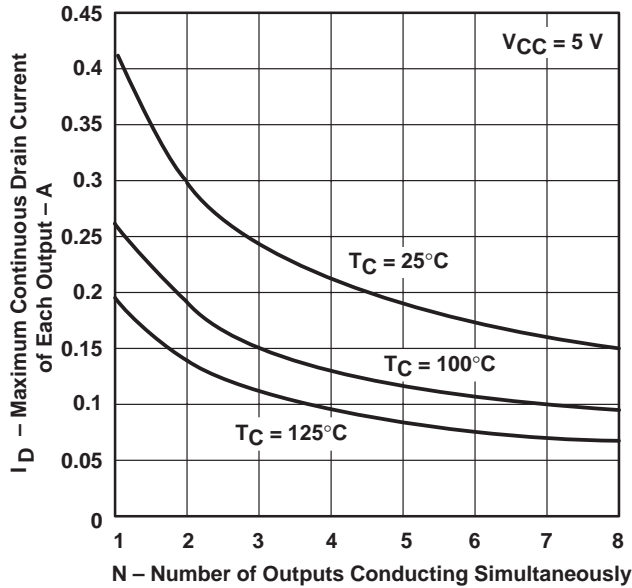


Figure 9

**MAXIMUM PEAK DRAIN CURRENT
OF EACH OUTPUT
vs
NUMBER OF OUTPUTS CONDUCTING
SIMULTANEOUSLY**

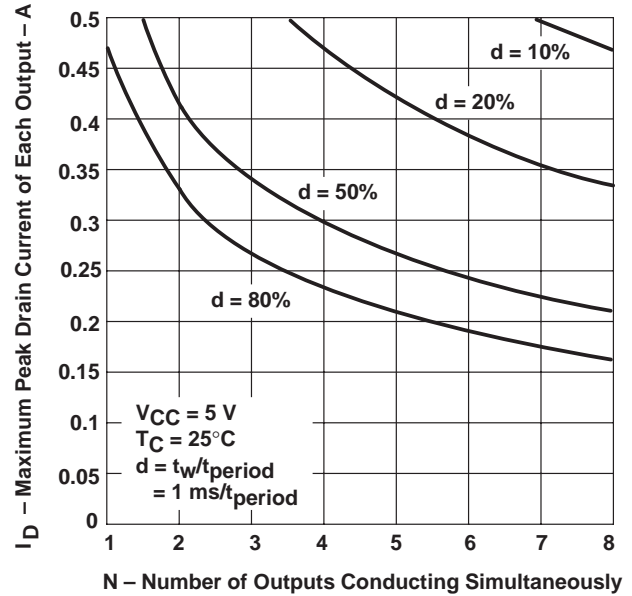


Figure 10

PACKAGING INFORMATION

| Orderable Device | Status (1) | Package Type | Package Drawing | Pins | Package Qty | Eco Plan (2) | Lead/Ball Finish | MSL Peak Temp (3) | Op Temp (°C) | Top-Side Markings (4) | Samples |
|------------------|---------------|--------------|--------------------|------|----------------|----------------------------|------------------|----------------------|--------------|--------------------------|-------------------------|
| TPIC6B273DW | ACTIVE | SOIC | DW | 20 | 25 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | -40 to 125 | TPIC6B273 | Samples |
| TPIC6B273DWG4 | ACTIVE | SOIC | DW | 20 | 25 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | | TPIC6B273 | Samples |
| TPIC6B273DWR | ACTIVE | SOIC | DW | 20 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | -40 to 125 | TPIC6B273 | Samples |
| TPIC6B273DWRG4 | ACTIVE | SOIC | DW | 20 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | | TPIC6B273 | Samples |
| TPIC6B273N | ACTIVE | PDIP | N | 20 | 20 | Pb-Free (RoHS) | CU NIPDAU | N / A for Pkg Type | -40 to 125 | TPIC6B273N | Samples |

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) Multiple Top-Side Markings will be inside parentheses. Only one Top-Side Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Top-Side Marking for that device.

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TAPE AND REEL INFORMATION

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE


*All dimensions are nominal

| Device | Package Type | Package Drawing | Pins | SPQ | Reel Diameter (mm) | Reel Width W1 (mm) | A0 (mm) | B0 (mm) | K0 (mm) | P1 (mm) | W (mm) | Pin1 Quadrant |
|----------------|--------------|-----------------|------|------|--------------------|--------------------|---------|---------|---------|---------|--------|---------------|
| TPIC6B273DWR | SOIC | DW | 20 | 2000 | 330.0 | 24.4 | 10.8 | 13.3 | 2.7 | 12.0 | 24.0 | Q1 |
| TPIC6B273DWRG4 | SOIC | DW | 20 | 2000 | 330.0 | 24.4 | 10.8 | 13.3 | 2.7 | 12.0 | 24.0 | Q1 |

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

| Device | Package Type | Package Drawing | Pins | SPQ | Length (mm) | Width (mm) | Height (mm) |
|----------------|--------------|-----------------|------|------|-------------|------------|-------------|
| TPIC6B273DWR | SOIC | DW | 20 | 2000 | 350.0 | 350.0 | 43.0 |
| TPIC6B273DWRG4 | SOIC | DW | 20 | 2000 | 350.0 | 350.0 | 43.0 |

N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



- NOTES:
- A. All linear dimensions are in inches (millimeters).
 - B. This drawing is subject to change without notice.
 - (C) Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
 - (D) The 20 pin end lead shoulder width is a vendor option, either half or full width.

DW0020A



PACKAGE OUTLINE

SOIC - 2.65 mm max height

SOIC



NOTES:

1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm per side.
5. Reference JEDEC registration MS-013.

EXAMPLE BOARD LAYOUT

DW0020A

SOIC - 2.65 mm max height

SOIC



LAND PATTERN EXAMPLE
SCALE:6X



SOLDER MASK DETAILS

4220724/A 05/2016

NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DW0020A

SOIC - 2.65 mm max height

SOIC



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:6X

4220724/A 05/2016

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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